

/ Descriptions

WR0<50 P ММ Ё QSQ æ Ñ ç s ll 1 Silicon NPN transistor in a TO-92LM Plastic Package.

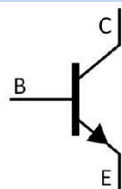
/ Features

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High breakdown voltage, low output capacitance, high f_T .

/ Applications

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TV video output, high voltage switching and driver stage of audio amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	70 140	120 240

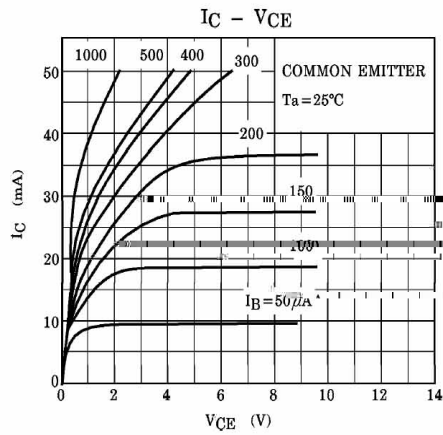
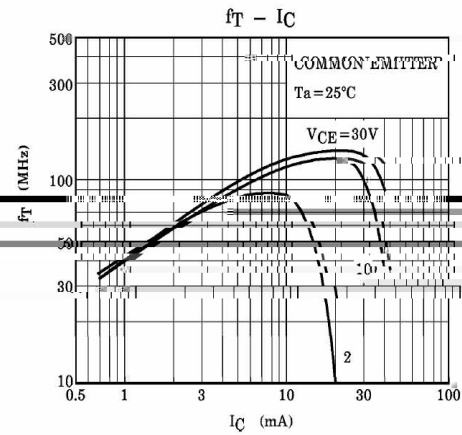
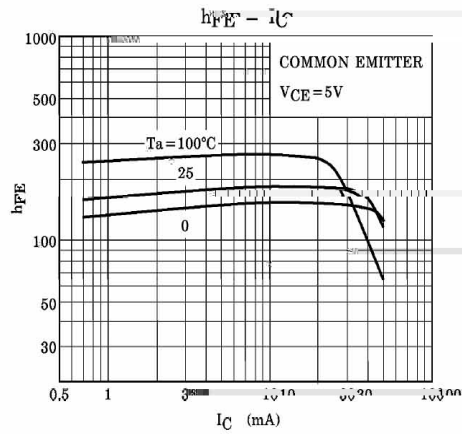
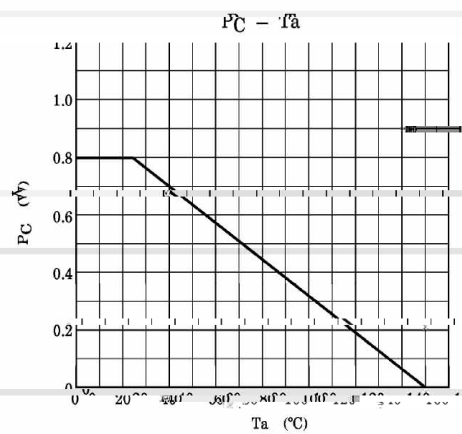
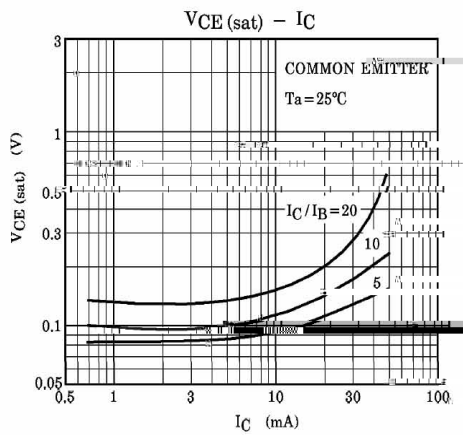
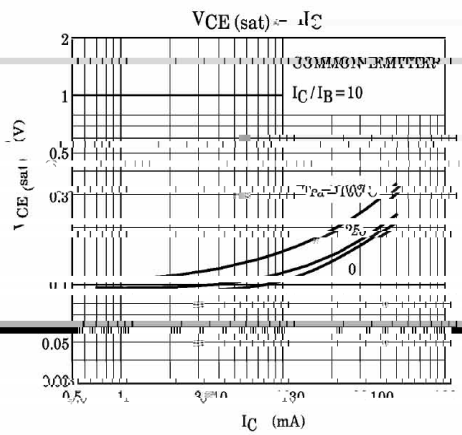
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	50	mA
Emitter Current	I_E	-50	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=200V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA

DC Current Gain

h_{FE} 0 7.02 238.56 394.40 399892003 T_c0 T_w6C

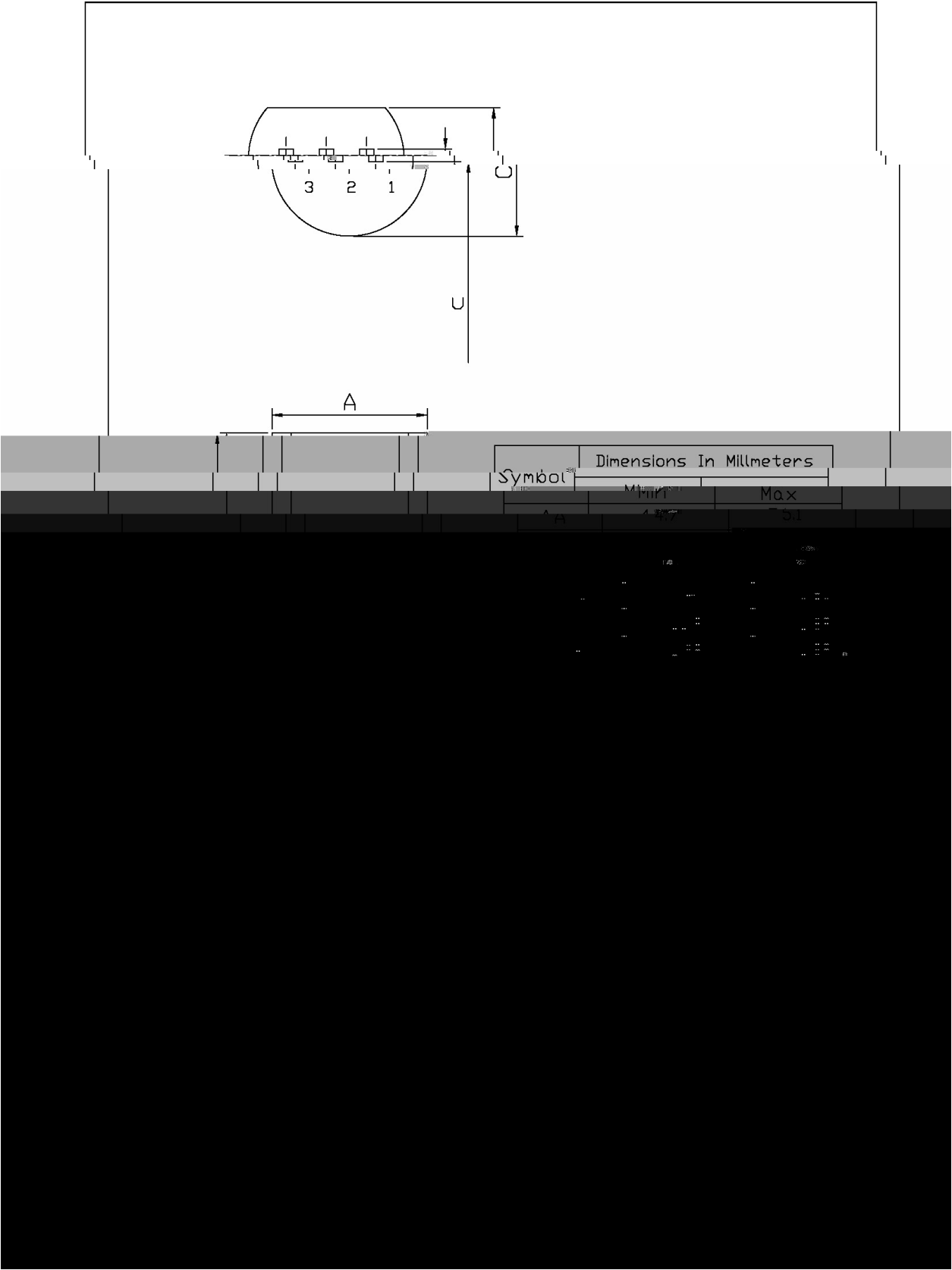
/ Electrical Characteristic Curve



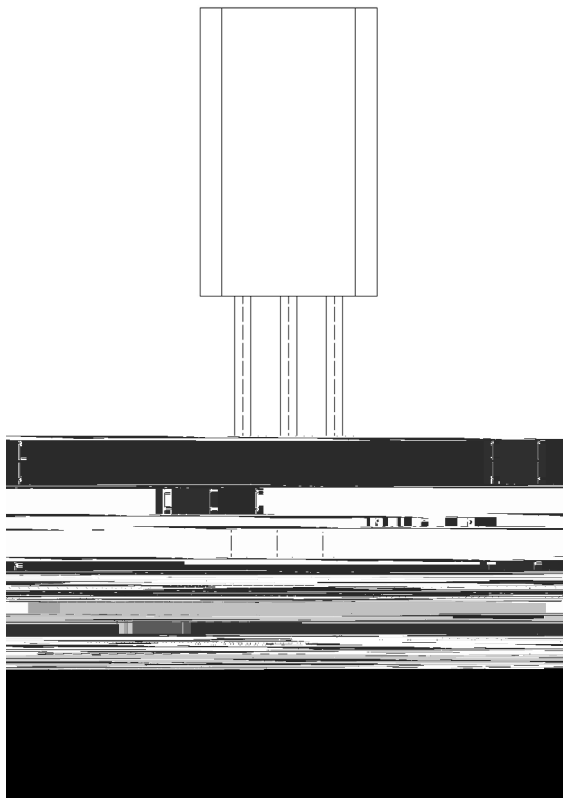
/ Package Dimensions

T0-92LM

Unit: mm



/ Marking Instructions



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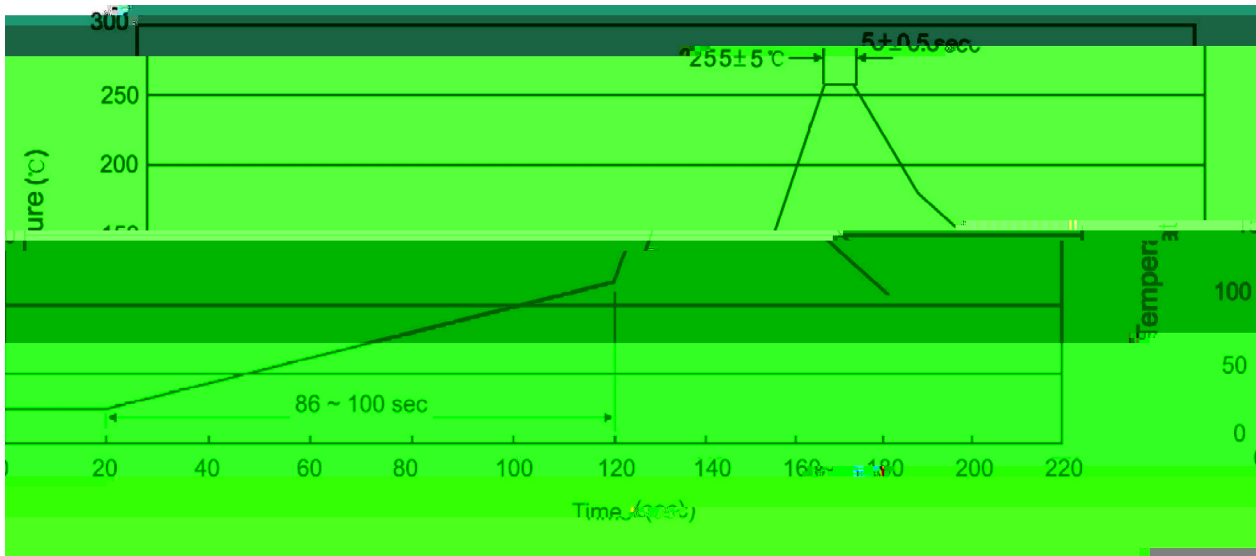
EU:

F555<X

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() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 255±5℃, 时间: 5±0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 255±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5℃ 时间: 10±1 sec. Temp.: 270±5 Time: 10±1 sec

/ Packaging SPEC.

包装形式 / BULK